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TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC4604

Power Amplifier Application.

Power Switching Applications.

• Low collector-emitter saturation voltage: V_{CE} (sat) = 0.5 V (max)

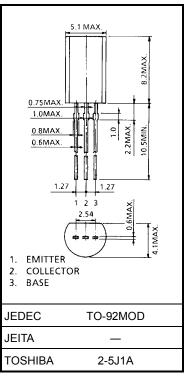
$$IC = 1.5 A$$
)

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- High-speed switching: $t_{stg} = 0.5 \ \mu s \ (typ.)$
- Complementary to 2SA1761

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	80	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	6	V	
Collector current	Ι _C	3	А	
Base current	Ι _Β	0.6	А	
Collector power dissipation	P _C	900	mW	
Junction temperature	Тј	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Electrical Characteristics (Ta = 25°C)

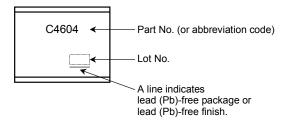
Weight: 0.36 g (typ.)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I _{CBO}	V _{CB} = 80 V, I _E = 0	_	_	0.1	μA
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 6 V, I _C = 0		-	0.1	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 10 mA, I _E = 0	50	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 100 mA	120	-	400	
		h _{FE (2)}	V _{CE} = 2 V, I _C = 2 A	40	-	_	
Collector-emitter	saturation voltage	V _{CE (sat)}	I _C = 1.5 A, I _B = 75 mA	_	_	0.5	V
Base-emitter satu	iration voltage	V _{BE (sat)}	I _C = 1.5 A, I _B = 75 mA	_	_	1.2	V
Transition freque	псу	f _T	V _{CE} = 2 V, I _C = 100 mA		100	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	20	_	pF
-	Turn-on time	t _{on}	$20 \ \mu s$ $Input$ I	_	0.1	_	
	Storage time	t _{stg}		_	0.5	_	μs
	Fall time	t _f		_	0.1	_	

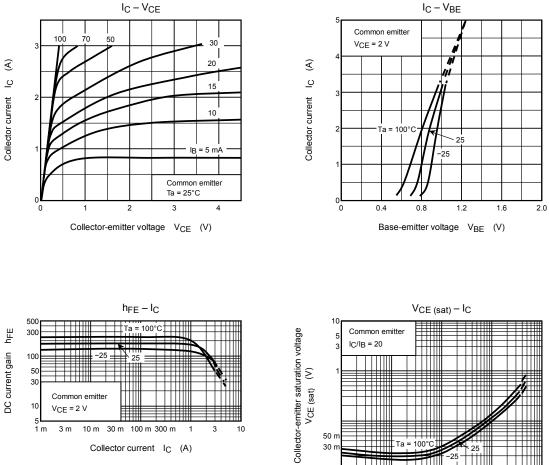
Unit: mm

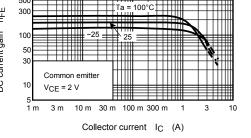
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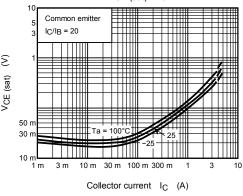
Marking

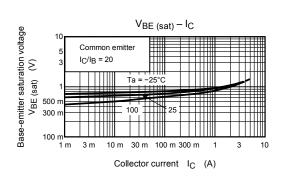


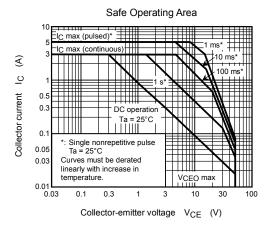
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